DC COMPONENTS CO., LTD.

RECTIFIER SPECIALISTS

1N60P

TECHNICAL SPECIFICATIONS OF SMALL SIGNAL SCHOTTKY DIODES

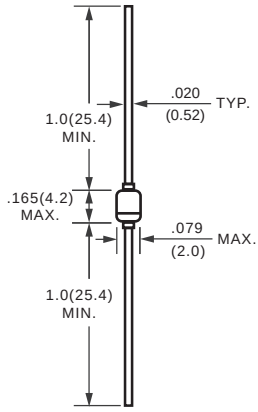
FEATURES

* Metal silicon junction, majority carrier conduction.
* High current capability, low forward voltage drop.
* Extremely low reverse current I_R
* Ultra speed switching characteristics
* Small temperature coefficient of forward characteristics
* Satisfactory Wave detection efficiency
* For use in RECORDER, TV, RADIO, TELEPHONE as detectors, super high speed switching circuits, small current rectifier

MECHANICAL DATA

* Case: DO-35 glass case
* Polarity: color band denotes cathode end
* Weight: 0.13 grams approx.

DO-35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

ABSOLUTE RATINGS(LIMITING VALUES)

PARAMETERS		SYMBOL	VALUE	UNITS
ZeneRepetitive Peak Reverse Voltage		V_{RRM}	45	Volts
Forward Continuous Current	T_A=25°C	I_F	50	mA
Peak Forward Surge Current(t=1S)		I_{FSM}	500	mA
Storage and junction Temperature Range		T_{STG}/T_J	-65 to +125	°C
Maximum Lead Temperature for Soldering during 10S at 4mm from Case		T_L	230	°C

ELECTRICAL CHARACTERISTICS

PARAMETERS	TEST CONDITIONS	SYMBOL	VALUE		UNITS
			TYP.	MAX.	
Forward Voltage	I_F=1mA	V_F	0.24	0.5	Volts
	I_F=200mA		0.65	1.0	
Reverse Current	V_R=15V	I_R	0.5	1.0	μA
Junction Capacitance	V_R=10V f=1MHz	C_J	6.0		pF
Detection Efficiency	V_I=3V f=30MHz C_L=10pF R_L=3.8KΩ	η	60		%
Reverse Recovey time	I_F=I_R=1mA I_{rr}=1mA R_C=100Ω	t_{rr}		1	ns
Junction Ambient Thermal Resistance		RθJA	400		°C/W

FIG.1-FORWARD CURRENT

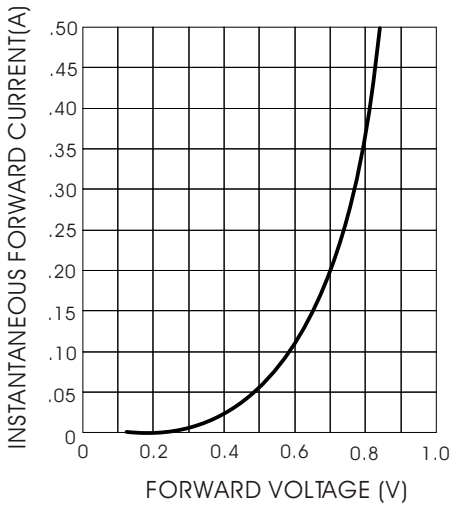


FIG.2-REVERSE CURRENT

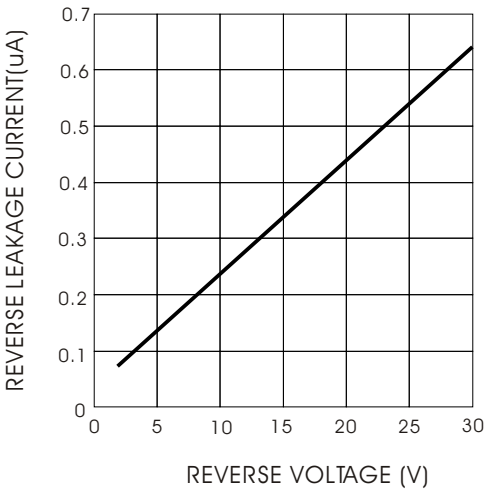


FIG.3-JUNCTION CAPACITANCE

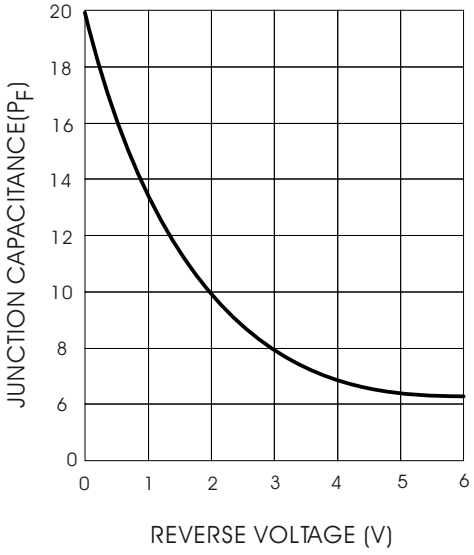


FIG.4-DETECTION EFFICIENCY MEEASUREMENT CIRCUIT